

Abstract

[0036] A heterojunction bipolar transistor (HBT), comprises a collector formed over
a substrate, a base formed over the collector, an emitter formed over the base, and a
tunneling suppression layer between the collector and the base, the tunneling
5 suppression layer fabricated from a material that is different from a material of the
base and that has an electron affinity equal to or greater than an electron affinity of
the material of the base.